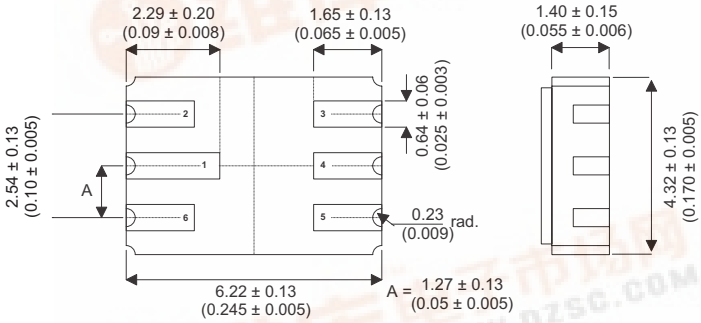
2N2916DCSM

DUAL NPN PLANAR TRANSISTORS IN A HERMETICALLY SEALED CERAMIC SURFACE MOUNT PACKAGE FOR HIGH RELIABILITY APPLICATIONS

MECHANICAL DATA
Dimensions in mm (inches)



LCC2 PACKAGE
Underside View

PAD 1 – Collector 1	**PAD 4 – Collector 2**
PAD 2 – Base 1	**PAD 5 – Emitter 2**
PAD 3 – Base 2	**PAD 6 – Emitter 1**

FEATURES

- **Hermetic Ceramic Surface Mount Package**
- **CECC Screening Options**
- **Space Quality Levels Options**

ABSOLUTE MAXIMUM RATINGS

	(T_{amb} = 25°C unless otherwise stated)		EACH SIDE	TOTAL DEVICE
V_{CBO}	Collector – Base Voltage		45V	
V_{CEO}	Collector – Emitter Voltage [1]		45V	
V_{EBO}	Emitter – Base Voltage		6V	
I_C	Continuous Collector Current		30	
P_D	Total Device Dissipation	T_{AMB} = 25°C	300mW	500mW
		Derate above 25°C	1.72mW / °C	2.86W / °C
T_{STG}	Storage Temperature Range		–65 to 200°C	
T_L	Lead temperature (Soldering, 10 sec.)		300°C	

NOTES

1 Base – Emitter Diode Open Circuited.

SEME LAB

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ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C unless otherwise stated)

Parameter		Test Conditions [1]		Min.	Typ.	Max.	Unit
INDIVIDUAL TRANSISTOR CHARACTERISTICS							
$V_{(BR)CBO}$	Collector – Base Breakdown Voltage	I_C = 10mA	I_E = 0	45			V
$V_{(BR)CEO}$*	Collector – Emitter Breakdown Voltage	I_C = 10mA	I_B = 0	45			
$V_{(BR)EBO}$	Emitter – Base Breakdown Voltage	I_E = 10mA	I_C = 0	6			
I_{CBO}	Collector Cut-off Current	V_{CB} = 45V	I_E = 0			10	nA
			T_A = 150°C			10	µA
I_{CEO}	Collector Cut-off Current	V_{CE} = 5V	I_B = 0			2	nA
I_{EBO}	Emitter Cut-off Current	V_{EB} = 5V	I_C = 0			2	
h_{FE}	DC Current Gain	V_{CE} = 5V	I_C = 10mA	150		600	—
			T_A = –55°C	30			
		V_{CE} = 5V	I_C = 100mA	225			
		V_{CE} = 5V	I_C = 1mA	300			
V_{BE}	Base – Emitter Voltage	V_{CE} = 5V	I_C = 100mA			0.70	V
$V_{CE(sat)}$	Collector – Emitter Saturation Voltage	I_B = 100mA	I_C = 1mA			0.35	
h_{ib}	Small Signal Common – Base Input Impedance	V_{CB} = 5V f = 1kHz	I_C = 1mA	25		32	Ω
h_{ob}	Small Signal Common – Base Output Admittance	V_{CB} = 5V f = 1kHz	I_C = 1mA			1	µmho
$\|h_{fe}\|$	Small Signal Common – Base Current Gain	V_{CE} = 5V f = 20MHz	I_C = 500mA	3			—
C_{obo}	Common – Base Open Circuit Output Capacitance	V_{CB} = 5V f = 140kHz to 1MHz	I_E = 0			6	pF
TRANSISTOR MATCHING CHARACTERISTICS							
$\frac{h_{FE1}}{h_{FE2}}$	Static Forward Current Gain Balance Ratio	V_{CE} = 5V See Note 2.	I_C = 100µA	0.9		1	—
$\|V_{BE1} - V_{BE2}\|$	Base – Emitter Voltage Differential	V_{CE} = 5V	I_C = 100µA			3	mV
		V_{CE} = 5V	I_C = 10µA to 1mA			5	
$\|D(V_{BE1} - V_{BE2})DT_A\|$	Base – Emitter Voltage Differential Change With Temperature	V_{CE} = 5V T_{A1} = 25°C	I_C = 100µA T_{A2} = –55°C			0.8	mV
		V_{CE} = 5V T_{A1} = 25°C	I_C = 100µA T_{A2} = 125°C			1	

* Pulse Test: t_p = 300µs , $\delta \leq 1\%$.

NOTES

1) Terminals not under test are open circuited under all test conditions.
2) The lower of the two readings is taken as h_{FE1}.